TOSHIBA CCD LINEAR IMAGE SENSOR CCD(Charge Coupled Device)

# **TCD1208AP**

The TCD1208AP is a high sensitive and low dark current 2160–element image sensor. The sensor can be used for facsimile, imagescanner and OCR. The device contains a row of 2160 photodiodes, which provide a 8 lines / mm (200 DPI) across a B4 size paper. The device is operated by 5V (pulse), and 5V power supply.

### **FEATURES**

• Number of Image Sensing Elements : 2160

• Image Sensing Element Size : 14µm by 14µm on

14µm centers

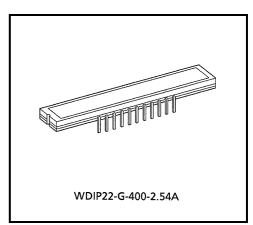
Photo Sensing Region : High sensitive, Low

dark current

• Clock : 2 phase (5V)

• Package : 22 pin DIP (T-CAPP)

TOSHIBA-CCD-ADVANCED-PLASTIC-PACKAGE



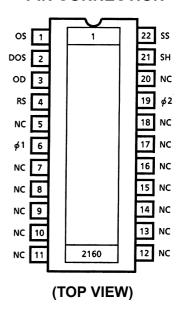
Weight: 2.7g (Typ.)

# **MAXIMUM RATINGS (Note 1)**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Clock Pulse Voltage	Vφ		<b>&gt;</b>
Shift Pulse Voltage	V <sub>SH</sub>	-0.3~8	
Reset Pulse Voltage	V <sub>RS</sub>	0.5 0	V
Power Supply Voltage	V <sub>OD</sub>		
Operating Temperature	T <sub>opr</sub>	-25~60	°C
Storage Temperature	T <sub>stg</sub>	-40~100	°C

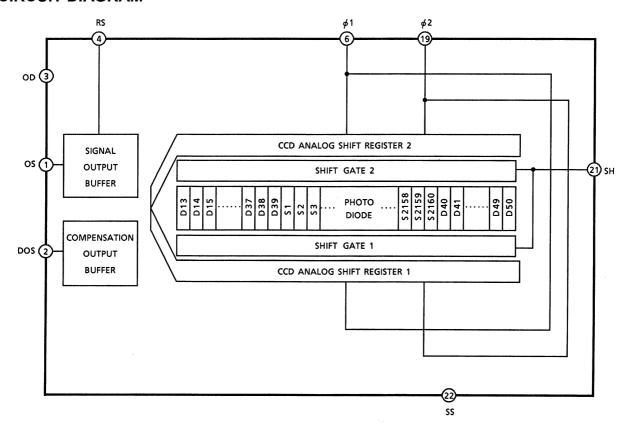
Note 1: All voltage are with respect to SS terminals (Ground).

# **PIN CONNECTION**



1 2001-10-15

# **CIRCUIT DIAGRAM**



2

## **PIN NAMES**

φ1	Clock (Phase 1)
φ2	Clock (Phase 2)
SH	Shift Gate
RS	Reset Gate
os	Signal Output
DOS	Compensation Output
OD	Power
SS	Ground
NC	Non Connection

# **OPTICAL / ELECTRICAL CHARACTERISTICS**

(Ta = 25°C,  $V_{OD}$  = 5V,  $V_{\phi}$  =  $V_{SH}$  =  $V_{RS}$  = 5V (PULSE),  $f_{\phi}$  = 0.5MHz,  $f_{RS}$  = 1MHz, LOAD RESISTANCE = 100k $\Omega$ ,  $t_{INT}$  (INTEGRATION TIME) = 10ms, LIGHT SOURCE = DAYLGIHT FLUORESCENT LAMP)

CHARACTERISTIC	SYMBOL	MIN	TYP.	MAX	UNIT	NOTE
Sensitivity	R	82	110	138	V / Ix·s	(Note 2)
Photo Response Non Uniformity	PRNU (1)	_	_	10	%	(Note 3)
Prioto Response Non Onnormity	PRNU (3)	_	7	16	mV	(Note 10)
Register Imbalance	RI	_	_	3	%	(Note 4)
Saturation Output Voltage	V <sub>SAT</sub>	0.6	1.5	_	V	(Note 5)
Saturation Exposure	SE	_	0.01	_	lx⋅s	(Note 6)
Dark Signal Voltage	$V_{DRK}$	_	2	6	mV	(Note 7)
Dark Signal Non Uniformity	DSNU	_	3	7	mV	(Note 7)
DC Power Dissipation	PD	_	50	100	mW	
Total Transfer Efficiency	TTE	92	_	_	%	
Output Impedance	Z <sub>O</sub>	_	_	1	kΩ	
Dynamic Range	DR	_	750	_	_	(Note 8)
DC Signal Output Voltage	Vos	3	3.5	4.5	V	(Note 9)
DC Compensation Output Voltage	V <sub>DOS</sub>	3	3.5	4.5	V	(Note 9)
DC Mismatch Voltage	Vos-V <sub>DOS</sub>	_	50	100	mV	(Note 11)
Random Noise	$ND_{\sigma}$	_	1.7	_	mV	(Note 12)

Note 2: Sensitivity for 2854K W-Lamp is 330V / lx·s (Typ.) Sensitivity for LED (567nm) is 71V / Ix·s (Typ.)

Note 3: Measured at 50% of SE (Typ.)

Definition of PRNU: PRNU =  $\frac{\Delta \chi}{\overline{\chi}} \times 100(\%)$ 

Where  $\bar{\chi}$  is average of total signal outputs and  $\Delta \chi$  is the maximum deviation from  $\bar{\chi}$  under uniform illumination.

Note 4: Measured at 50% of SE (Typ.)

RI is defined as follows:

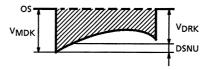
RI = 
$$\frac{\sum_{\sum_{j=1}^{2159} |\chi n - \chi n + 1|}{\sum_{j=1}^{2159 \times \sqrt{\chi}}} \times 100(\%)$$

Where  $\chi$  n and  $\chi$  n+1 are signal outputs of each pixel.  $\bar{\chi}$  is average of total signal outputs.

Note 5: V<sub>SAT</sub> is defined as minimum Saturation Output Voltage of all effective pixels.

Note 6: Definition of SE : SE =  $\frac{V_{SAT}}{R}$ 

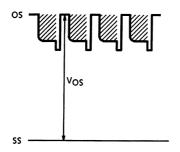
Note 7:  $V_{DRK}$  is defined as average dark signal voltage of all effective pixels. DSNU is defined as different voltage between  $V_{DRK}$  and  $V_{MDK}$ , when  $V_{MDK}$  is maximum dark voltage.

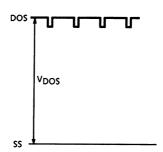


Note 8: Definition of DR : DR =  $\frac{V_{SAT}}{V_{DRK}}$ 

 $V_{\mbox{\footnotesize{DRK}}}$  is proportional to  $t_{\mbox{\footnotesize{INT}}}$  (Integration time). So the shorter  $t_{\mbox{\footnotesize{INT}}}$  is, the wider DR is.

Note 9: DC Signal Output Voltage and DC Compensation Output Voltage are defined as follows:





Note 10: PRNU (3) is defined as maximum voltage with next pixel where measured 5% of SE (Typ.).

Note 11: V<sub>OD</sub> = 4.7V DC Mismatch Voltage.

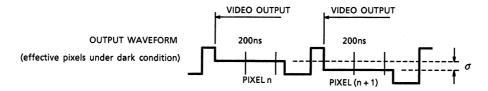
Note 12:

#### 1. DEFINITION

Random noise is defined as the standard deviation (sigma) of the output level difference between two adjacent effective pixels under no illumination (i.e. dark condition) calculated by the following procedure.

### 2. CALCULATION PROCEDURE

The following is the calculation procedure of random noise.



- 1) Two adjacent pixels (pixel n and n+1) in one reading are fixed as measurement points.
- 2) Each of the output levels at video output period is averaged over 200 nanosecond period to get Vn and Vn+1.
- 3) Vn+1 is subtracted from Vn to get  $\Delta V$ .

$$\Delta V = Vn-Vn+1$$

4) The standard deviation of  $\Delta V$  is calculated after procedure 2) and 3) are repeated 30 times (30 readings).

$$\overline{\Delta V} = \frac{1}{30} \sum_{i=1}^{30} \left| \Delta V^i \right| \qquad \sigma = \sqrt{\frac{1}{30} \sum_{j=1}^{30} \left( \left| \Delta V^i \right| - \overline{\Delta V} \right)^2}$$

5) Procedure 2), 3) and 4) are repeated 10 times to get 10 sigma values.

$$\overline{\sigma} = \frac{1}{10} \sum_{j=1}^{10} \sigma_j$$

6)  $\bar{\sigma}$  value calculated using the above procedure is observed  $\sqrt{2}$  times larger than that measured relative to the ground level. So we specify the random noise as the following.

Random noise 
$$(N_{D\sigma}) = \frac{1}{\sqrt{2}}\bar{\sigma}$$

# **OPERATING CONDITION**

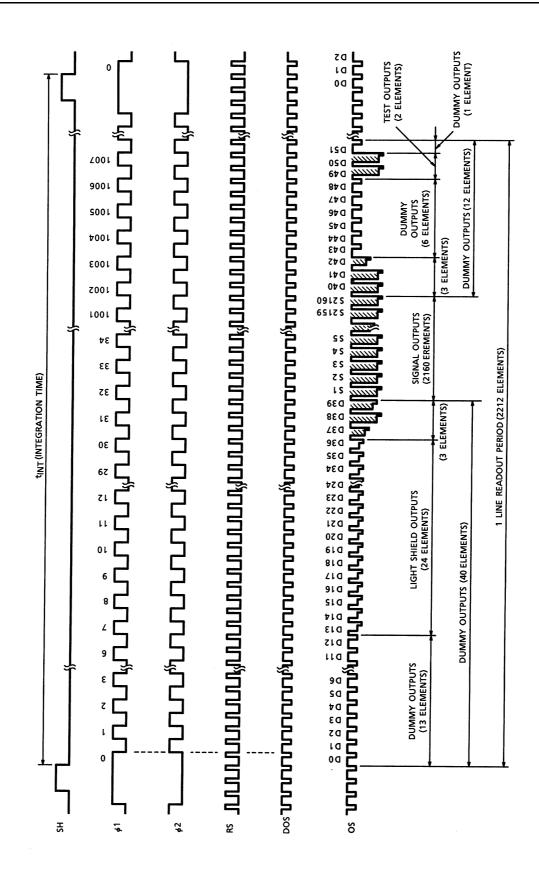
CHARACTERISTIC		SYMBOL	MIN	TYP.	MAX	UNIT
Clock Pulse Voltage	"H" Level	Vφ	4.5	5	5.5	V
Clock Pulse Voltage	"L" Level		0	0	0.3	
Shift Pulse Voltage	"H" Level	V <sub>SH</sub>	4.5	5	5.5	V
Shiit Fuise Voltage	"L" Level		0	0	0.3	
Reset Pulse Voltage	"H" Level	) /	4.7	5	5.5	V
Reset Fulse Voltage	"L" Level	V <sub>RS</sub>	0	0	0.3	٧
Power Supply Voltage		V <sub>OD</sub>	4.7	5.0	5.3	V

# CLOCK CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	MIN	TYP.	MAX	UNIT
Clock Pulse Frequency	$f_{oldsymbol{\phi}}$	0.15	0.5	1.0	MHz
Reset Pulse Frequency	f <sub>RS</sub>	0.3	1.0	2.0	MHz
Clock Capacitance	Сф	_	200	300	pF
Shift Gate Capacitance	C <sub>SH</sub>	_	100	200	pF
Reset Gate Capacitance	C <sub>RS</sub>	_	10	30	pF

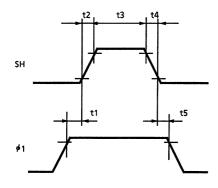
6



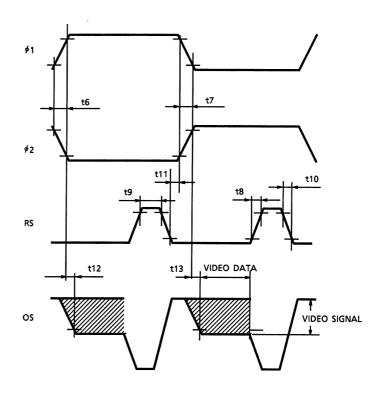


# **TIMING REQUIREMENTS**

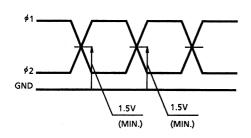
SH, *ϕ*1 Timing



 $\phi$ 1,  $\phi$ 2, RS, OS Timing



ø1, ø2 Cross Point

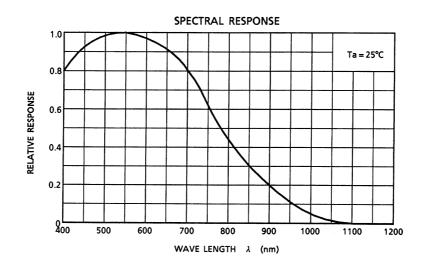


CHARACTERISTIC	SYMBOL	MIN	TYP. (Note 13)	MAX	UNIT
Pulse Timing of SH and $_\phi$ 1	t1, t5	0	100	_	ns
SH Pulse Rise Time, Fall Time	t2, t4	0	50	_	ns
SH Pulse Width	t3	500	1000	_	ns
$_{\phi}$ 1 $_{\phi}$ 2 Pulse Rise Time, Fall Time	t6, t7	0	60	100	ns
RS Pulse Rise Time, Fall Time	t8, t10	0	20	_	ns
RS Pulse Width	t9	40	250	_	ns
Pulse Timing of $_\phi$ 1, $_\phi$ 2 and RS	t11	230	_	_	ns
Video Data Delay Time (Note 14)	t12, t13	_	150	_	ns

Note 13: TYP. is the case of  $f_{RS}$  = 1MHz Note 14: Load Resistance is  $100k\Omega$ 

8

# **TYPICAL PERFORMANCE CURVES**



1.0

9



SPATIAL FREQUENCY (Cycles/mm)

0 7.1 14.3 21.4 28.6 35.7

1.0

0.8

λ = 550nm

×

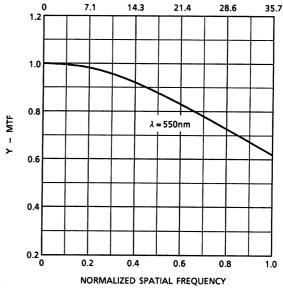
0.6

NORMALIZED SPATIAL FREQUENCY

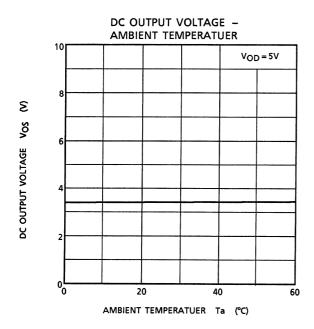
0.2<mark>L</mark>

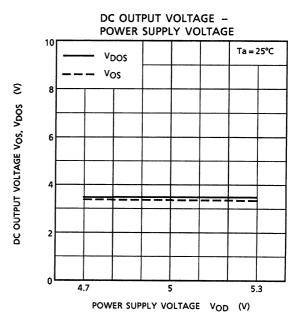
# MODULATION TRANSFER FUNCTION OF Y-DIRECTION

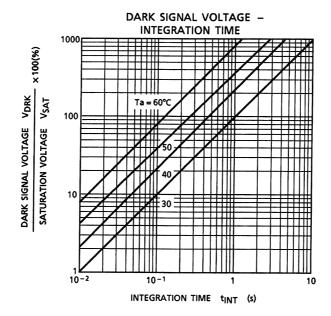




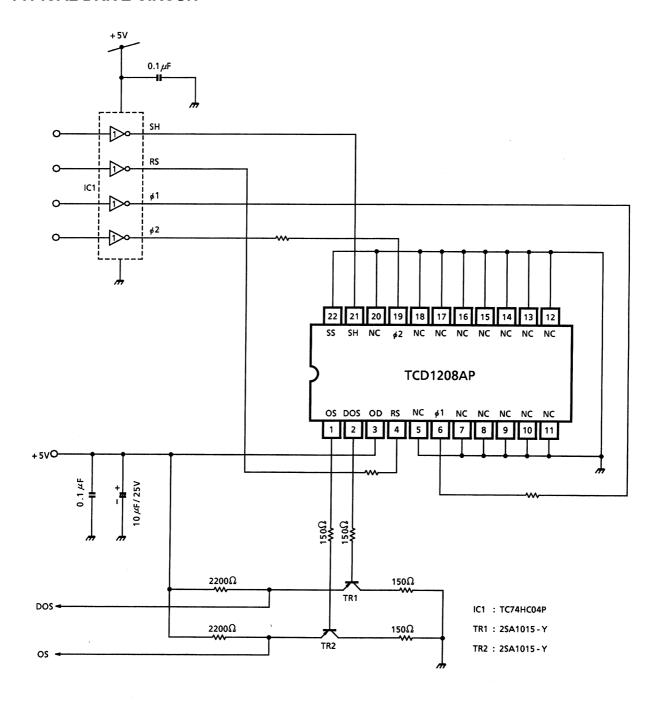
## **TYPICAL PERFORMANCE CURVES**







# **TYPICAL DRIVE CIRCUIT**



### **CAUTION**

### 1. Window Glass

The dust and stain on the glass window of the package degrade optical performance of CCD sensor. Keep the glass window clean by saturating a cotton swab in alcohol and lightly wiping the surface, and allow the glass to dry, by blowing with filtered dry N2. Care should be taken to avoid mechanical or thermal shock because the glass window is easily to damage.

#### 2. Electrostatic Breakdown

Store in shorting clip or in conductive foam to avoid electrostatic breakdown.

CCD Image Sensor is protected against static electricity, but interior puncture mode device due to static electricity is sometimes detected. In handing the device, it is necessary to execute the following static electricity preventive measures, in order to prevent the trouble rate increase of the manufacturing system due to static electricity.

- a. Prevent the generation of static electricity due to friction by making the work with bare hands or by putting on cotton gloves and non-charging working clothes.
- Discharge the static electricity by providing earth plate or earth wire on the floor, door or stand of the work room.
- c. Ground the tools such as soldering iron, radio cutting pliers of or pincer.
   It is not necessarily required to execute all precaution items for static electricity.
   It is all right to mitigate the precautions by confirming that the trouble rate within the prescribed range.

### 3. Incident Light

CCD sensor is sensitive to infrared light. Note that infrared light component degrades resolution and PRNU of CCD sensor.

### 4. Lead Frame Forming

Since this package is not strong against mechanical stress, you should not reform the lead frame. We recommend to use a IC-inserter when you assemble to PCB.

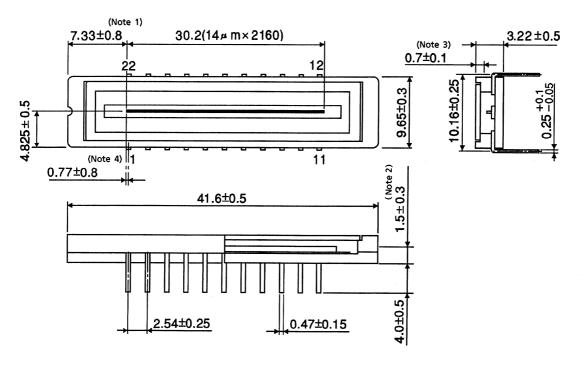
### 5. Soldering

Soldering by the solder flow method cannot be guaranteed because this method may have deleterious effects on prevention of window glass soiling and heat resistance.

Using a soldering iron, complete soldering within ten seconds for lead temperatures of up to 260°C, or within three seconds for lead temperatures of up to 350°C.

# **PACKAGE DIEMENSIONS**

WDIP22-G-400-2.54A Unit: mm



Note 1: No. 1 SENSOR ELEMENT (S1) TO EDGE OF PACKAGE.

Note 2: TOP OF CHIP TO BOTTOM OF PACKAGE.

Note 3: GLASS THICKNES (n = 1.5)

Note 4: No. 1 SENSOR ELEMENT (S1) TO CENTER OF No. 1 PIN.

Weight: 2.7g (Typ.)

### **RESTRICTIONS ON PRODUCT USE**

000707EBA

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The products described in this document are subject to the foreign exchange and foreign trade laws.
- The information contained herein is presented only as a guide for the applications of our products. No
  responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other
  rights of the third parties which may result from its use. No license is granted by implication or otherwise under
  any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.